

GaN Amplifier 65 V, 2600 W 960 - 1215 MHz



MACOM PURE CARBIDE™

MAPC-A1500

Rev. V5

Features

- MACOM PURE CARBIDE™ Amplifier Series
- Suitable for Linear & Saturated Applications
- Pulsed Operation: 2600 W Output Power @ 65 V
2000 W Output Power @ 50 V
- Internally Pre-Matched
- 260°C Reflow Compatible
- 65 V Operation
- 100% RF Tested
- RoHS* Compliant
- Compatible with MACOM Power Management Bias Controller/Sequencer MABC-11040

Applications

- Avionics, IFF Transponders.

Description

The MAPC-A1500 is a high power GaN on Silicon Carbide HEMT D-mode amplifier suitable for 960 - 1215 MHz frequency operation. The device supports pulsed operation with output power levels of 2600 W (64.1 dBm) at 65 V and 2000 W (63.0 dBm) at 50 V and in an air cavity ceramic package.

Typical Performance:

Measured under load-pull at 2.5 dB Compression, 100 μ s pulse width, 1% duty cycle.

- $V_{DS} = 65$ V, $I_{DQ} = 1300$ mA, $T_C = 25^\circ$ C

Frequency (MHz)	Output Power ¹ (dBm)	Gain ² (dB)	η_D^2 (%)
960	65.4	20.8	76.1
1030	65.2	20.4	73.1
1090	65.1	20.4	73.1
1215	64.9	18.8	71.0

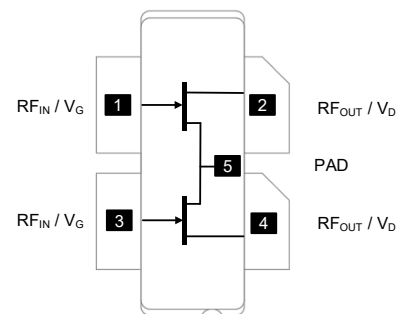
- $V_{DS} = 50$ V, $I_{DQ} = 1300$ mA, $T_C = 25^\circ$ C

Frequency (MHz)	Output Power ¹ (dBm)	Gain ² (dB)	η_D^2 (%)
960	64.1	19.9	71.2
1030	63.8	19.6	70.4
1090	63.7	19.1	70.7
1215	63.7	18.4	71.3

1. Load impedance tuned for maximum output power. Power is twice single side performance.
2. Load impedance tuned for maximum drain efficiency.



Functional Schematic



Pin Configuration

Pin #	Pin Name	Function
1, 3	RF _{IN} / V _G	RF Input / Gate
2, 4	RF _{OUT} / V _D	RF Output / Drain
5	Flange ³	Ground / Source

3. The flange on the package bottom must be connected to RF, DC and thermal ground.

Ordering Information

Part Number	Package
MAPC-A1500-AS000	Bulk Quantity: Earless
MAPC-A1500-ASTR1	Tape and Reel: Earless
MAPC-A1500-ASSB1	Sample Board: Earless
MAPC-A1500-AB000	Bulk Quantity: Boltdown
MAPC-A1500-ABTR1	Tape and Reel: Boltdown
MAPC-A1500-ABSB1	Sample Board: Boltdown

1 * Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

GaN Amplifier 65 V, 2600 W 960 - 1215 MHz



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Rev. V5

RF Electrical Characteristics: $T_C = 25^\circ\text{C}$, $V_{DS} = 65\text{ V}$, $I_{DQ} = 1300\text{ mA}$

Note: Performance in MACOM 1030-1090 MHz Evaluation Test Fixture, 50 Ω system

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Small Signal Gain	Pulsed ⁴ , 1.06 GHz	G_{SS}	-	18.3	-	dB
Saturated Output Power	Pulsed ⁴ , 1.06 GHz, 2.5 dB Gain Compression	P_{SAT}	-	64.2	-	dBm
Power Gain	Pulsed ⁴ , 1.06 GHz, 2.5 dB Gain Compression	G_{SAT}	-	18.5	-	dB
Saturated Drain Efficiency	Pulsed ⁴ , 1.06 GHz, 2.5 dB Gain Compression	η_{SAT}	-	66.2	-	%
Gain Variation (-40°C to +85°C)	Pulsed ⁴ , 1.06 GHz	ΔG	-	0.018	-	dB/°C
Power Variation (-40°C to +85°C)	Pulsed ⁴ , 1.06 GHz	$\Delta P_{2.5dB}$	-	0.005	-	dB/°C
Power Gain	Pulsed ⁴ , 1.06 GHz, $P_{OUT} = 64.1\text{ dBm}$	G_P	-	18.9	-	dB
Drain Efficiency	Pulsed ⁴ , 1.06 GHz, $P_{OUT} = 64.1\text{ dBm}$	η	-	65.0	-	%
Input Return Loss	Pulsed ⁴ , 1.06 GHz, $P_{OUT} = 64.1\text{ dBm}$	IRL	-	-10	-	dB
Ruggedness: Output Mismatch	All phase angles	Ψ	VSWR = 7:1, No Damage			

RF Electrical Characteristics: $T_C = 25^\circ\text{C}$, $V_{DS} = 50\text{ V}$, $I_{DQ} = 1300\text{ mA}$

Note: Performance in MACOM 1030-1090 MHz Evaluation Test Fixture, 50 Ω system

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Small Signal Gain	Pulsed ⁴ , 1.06 GHz	G_{SS}	-	16.8	-	dB
Saturated Output Power	Pulsed ⁴ , 1.06 GHz, 2.5 dB Gain Compression	P_{SAT}	-	63.1	-	dBm
Power Gain	Pulsed ⁴ , 1.06 GHz, 2.5 dB Gain Compression	G_{SAT}	-	16.9	-	dB
Saturated Drain Efficiency	Pulsed ⁴ , 1.06 GHz, 2.5 dB Gain Compression	η_{SAT}	-	58	-	%
Gain Variation (-40°C to +85°C)	Pulsed ⁴ , 1.06 GHz	ΔG	-	0.015	-	dB/°C
Power Variation (-40°C to +85°C)	Pulsed ⁴ , 1.06 GHz	$\Delta P_{2.5dB}$	-	0.005	-	dB/°C
Power Gain	Pulsed ⁴ , 1.06 GHz, $P_{OUT} = 63.0\text{ dBm}$	G_P	-	17.5	-	dB
Drain Efficiency	Pulsed ⁴ , 1.06 GHz, $P_{OUT} = 63.0\text{ dBm}$	η	-	57.5	-	%
Input Return Loss	Pulsed ⁴ , 1.06 GHz, $P_{OUT} = 63.0\text{ dBm}$	IRL	-	-10	-	dB
Ruggedness: Output Mismatch	All phase angles	Ψ	VSWR = 7:1, No Damage			

4. Pulse Details: 100 μs pulse width, 1% duty cycle.

RF Electrical Specifications: $T_A = 25^\circ\text{C}$, $V_{DS} = 65\text{ V}$, $I_{DQ} = 650\text{ mA}$

Note: Performance in MACOM 1030-1090 MHz Production Test Fixture, 50 Ω system

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Power Gain	Pulsed ⁴ , 1.06 GHz, 2.5 dB Gain Compression	G_{SAT}	17.5	18.5	-	dB
Saturated Drain Efficiency	Pulsed ⁴ , 1.06 GHz, 2.5 dB Gain Compression	η_{SAT}	61.6	66.2	-	%
Saturated Output Power	Pulsed ⁴ , 1.06 GHz, 2.5 dB Gain Compression	P_{SAT}	63	64.2	-	dBm

DC Electrical Characteristics $T_A = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Drain-Source Leakage Current	$V_{GS} = -8\text{ V}$, $V_{DS} = 130\text{ V}$	I_{DLK}	-	-	266	mA
Gate-Source Leakage Current	$V_{GS} = -8\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GLK}	-	-	266	mA
Gate Threshold Voltage	$V_{DS} = 50\text{ V}$, $I_D = 266\text{ mA}$	V_T	-3.6	-3.1	-	V
Gate Quiescent Voltage	$V_{DS} = 50\text{ V}$, $I_D = 1300\text{ mA}$	V_{GSQ}	-	-2.85	-	V
On Resistance	$V_{GS} = 2\text{ V}$, $I_D = 2000\text{ mA}$	R_{ON}	-	0.013	-	Ω
Maximum Drain Current	$V_{DS} = 7\text{ V}$ pulsed, pulse width 300 μs	$I_{D, MAX}$	-	253	-	A

Absolute Maximum Ratings ^{5,6,7,8,9}

Parameter	Absolute Maximum
Drain Source Voltage, V_{DS}	130 V
Gate Source Voltage, V_{GS}	-10 to 3 V
Gate Current, I_G	266 mA
Storage Temperature Range	-65°C to +150°C
Case Operating Temperature Range	-40°C to +85°C
Channel Operating Temperature Range, T_{CH}	-40°C to +225°C
Absolute Maximum Channel Temperature	+250°C

5. Exceeding any one or combination of these limits may cause permanent damage to this device.
6. MACOM does not recommend sustained operation above maximum operating conditions.
7. Operating at drain source voltage $V_{DS} < 55$ V will ensure $MTTF > 2 \times 10^6$ hours.
8. Operating at nominal conditions with $T_{CH} \leq 200^\circ\text{C}$ will ensure $MTTF > 2 \times 10^6$ hours.
9. MTTF may be estimated by the expression $MTTF \text{ (hours)} = A e^{\frac{B+C}{T+273}}$ where T is the channel temperature in degrees Celsius, $A = 1$, $B = -38.215$, and $C = 26,343$.

Thermal Characteristics ¹⁰

Parameter	Test Conditions	Symbol	Typical	Units
Thermal Resistance using Finite Element Analysis (Pulsed: 100µs, 10%)	$V_{DS} = 65$ V, $T_C = 85^\circ\text{C}$, $T_{CH} = 225^\circ\text{C}$	$R_{\theta}(\text{FEA})$	0.080	°C/W
Thermal Resistance using Infrared Measurement of Die Surface Temperature	$V_{DS} = 65$ V, $T_C = 85^\circ\text{C}$, $T_{CH} = 225^\circ\text{C}$	$R_{\theta}(\text{IR})$	0.074	°C/W

10. Case temperature measured using thermocouple embedded in heat-sink. Contact local applications support team for more details on this measurement.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

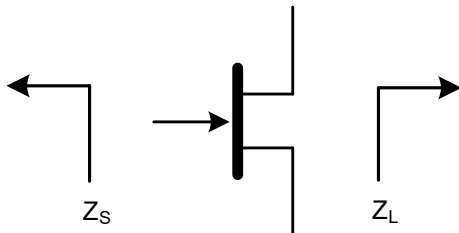
Gallium Nitride Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

65 V Pulsed¹³ Load-Pull Performance - Per Side
Reference Plane at Device Leads

Frequency (MHz)	Z_{SOURCE} (Ω)	Maximum Output Power					
		$V_{DS} = 65\text{ V}, I_{DQ} = 650\text{ mA}, T_C = 25^\circ\text{C}, P_{2.5dB}$					
		Z_{LOAD}^{11} (Ω)	Gain (dB)	P_{OUT} (dBm)	P_{OUT} (W)	η_D (%)	AM/PM ($^\circ$)
960	1.1 - j2.0	0.73 - j0.55	19.6	62.4	1740	65.8	32
1030	2.3 - j1.8	0.68 - j0.61	19.0	62.2	1660	62.5	-3
1090	2.6 - j0.8	0.64 - j0.62	18.7	62.1	1620	62.2	-32
1215	1.3 + j0.1	0.62 - j0.73	18.2	61.9	1550	63.7	-81

Frequency (MHz)	Z_{SOURCE} (Ω)	Maximum Drain Efficiency					
		$V_{DS} = 65\text{ V}, I_{DQ} = 650\text{ mA}, T_C = 25^\circ\text{C}, P_{2.5dB}$					
		Z_{LOAD}^{12} (Ω)	Gain (dB)	P_{OUT} (dBm)	P_{OUT} (W)	η_D (%)	AM/PM ($^\circ$)
960	1.1 - j2.2	0.85 + j0.24	20.8	60.0	1000	76.1	14
1030	2.6 - j1.5	0.87 + j0.08	20.4	60.0	1000	73.1	-30
1090	2.5 - j0.1	0.86 + j0.0	20.4	59.5	890	73.1	-69
1215	1.0 + j0.0	0.77 - j0.12	18.8	59.5	890	71.0	-106

Impedance Reference



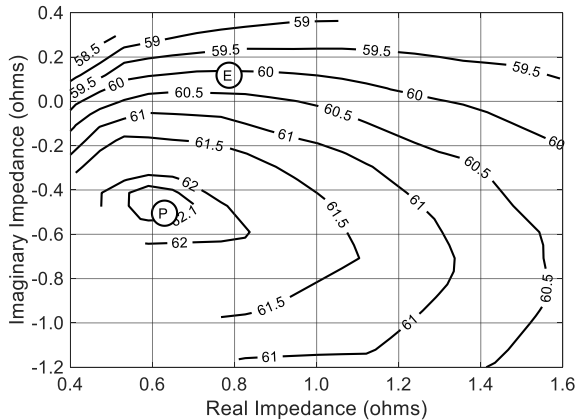
Z_{SOURCE} = Measured impedance presented to the input of the device at package reference plane.

Z_{LOAD} = Measured impedance presented to the output of the device at package reference plane.

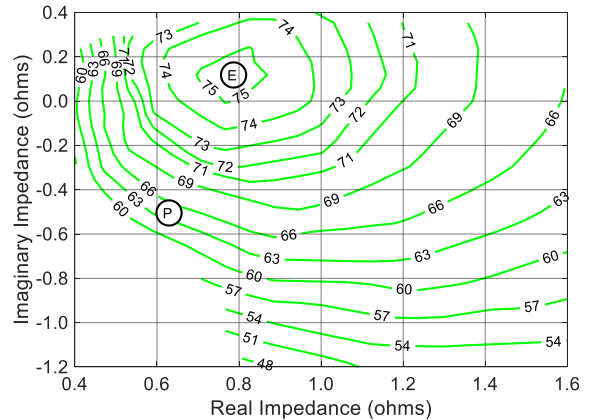
- 11. Load Impedance for optimum output power.
- 12. Load Impedance for optimum efficiency.
- 13. Pulse Details: 15 μs pulse width, 1% duty cycle

65 V Pulsed¹³ Load-Pull Performance
1090 MHz - Per Side

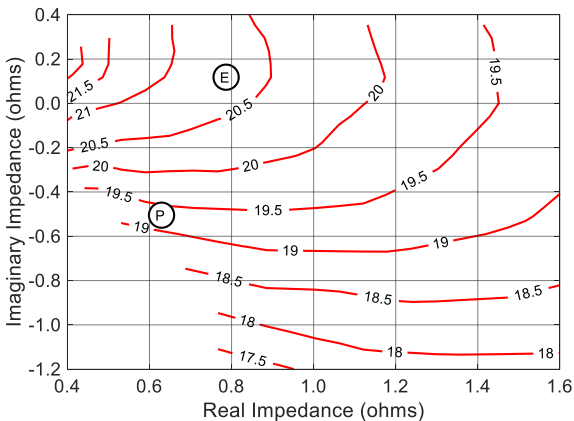
P2.5dB Loadpull Output Power Contours (dBm)



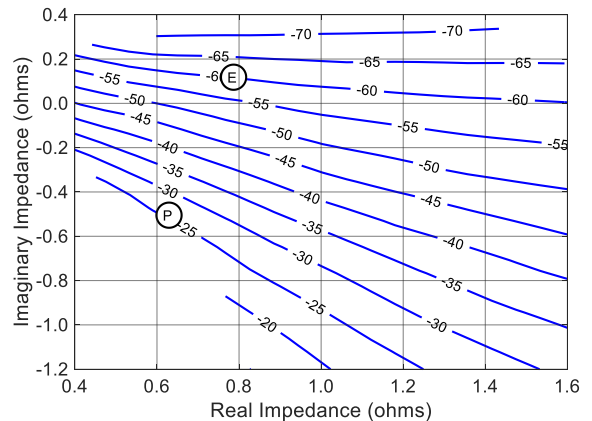
P2.5dB Loadpull Drain Efficiency Contours (%)



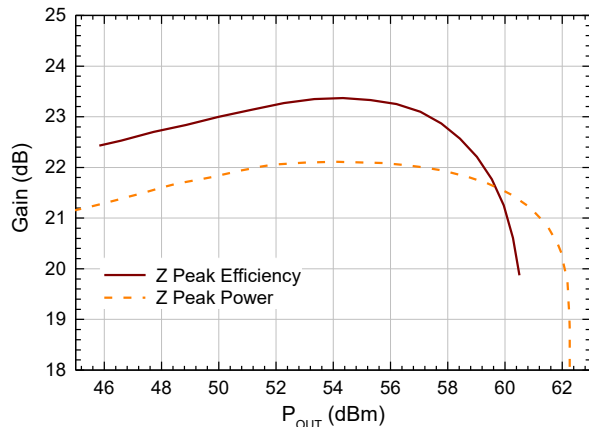
P2.5dB Loadpull Gain Contours (dB)



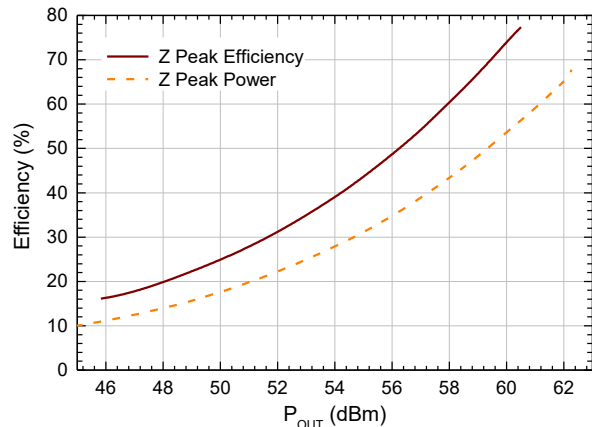
P2.5dB Loadpull AM/PM Contours (°)



Gain vs. Output Power



Drain Efficiency vs. Output Power

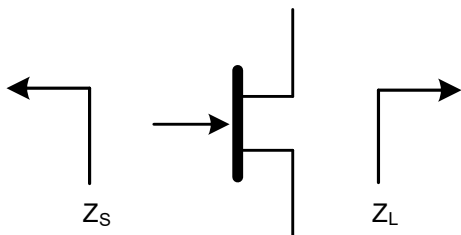


50 V Pulsed¹³ Load-Pull Performance - Per Side
Reference Plane at Device Leads

Frequency (MHz)	Z_{SOURCE} (Ω)	Maximum Output Power					
		$V_{DS} = 50\text{ V}, I_{DQ} = 650\text{ mA}, T_C = 25^\circ\text{C}, P_{2.5dB}$					
		Z_{LOAD}^{11} (Ω)	Gain (dB)	P_{OUT} (dBm)	P_{OUT} (W)	η_D (%)	AM/PM ($^\circ$)
960	1.2 - j2.2	0.55 - j0.54	19.1	61.1	1290	62.6	35
1030	2.6 - j1.2	0.54 - j0.81	18.4	60.8	1200	60.8	0
1090	2.5 + j0.3	0.49 - j0.80	18.4	60.7	1175	60.8	-32
1215	1.1 - j0.1	0.47 - j0.93	17.7	60.7	1175	59.7	-78

Frequency (MHz)	Z_{SOURCE} (Ω)	Maximum Drain Efficiency					
		$V_{DS} = 50\text{ V}, I_{DQ} = 650\text{ mA}, T_C = 25^\circ\text{C}, P_{2.5dB}$					
		Z_{LOAD}^{12} (Ω)	Gain (dB)	P_{OUT} (dBm)	P_{OUT} (W)	η_D (%)	AM/PM ($^\circ$)
960	1.2 - j2.2	0.91 + j0.07	19.9	58.5	710	71.2	7
1030	2.6 - j1.2	0.78 - j0.16	19.6	58.5	710	70.4	-36
1090	2.5 + j0.3	0.77 - j0.23	19.1	58.4	690	70.7	-69
1215	1.1 - j0.1	0.68 - j0.38	18.4	58.4	690	71.3	-106

Impedance Reference



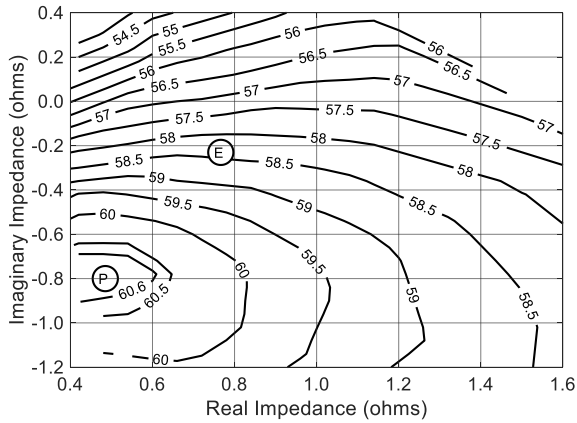
Z_{SOURCE} = Measured impedance presented to the input of the device at package reference plane.

Z_{LOAD} = Measured impedance presented to the output of the device at package reference plane.

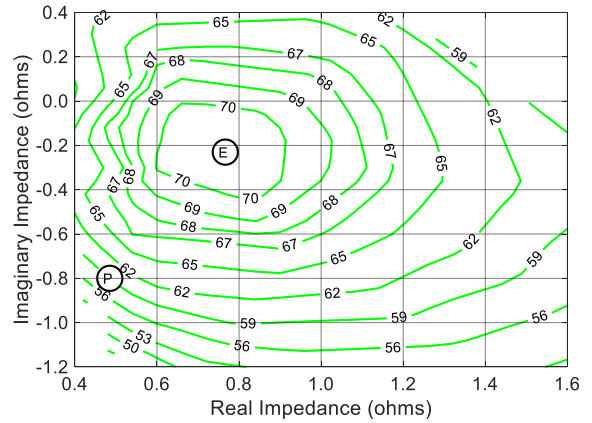
- 11. Load Impedance for optimum output power.
- 12. Load Impedance for optimum efficiency.

50 V Pulsed¹³ Load-Pull Performance
1090 MHz - Per Side

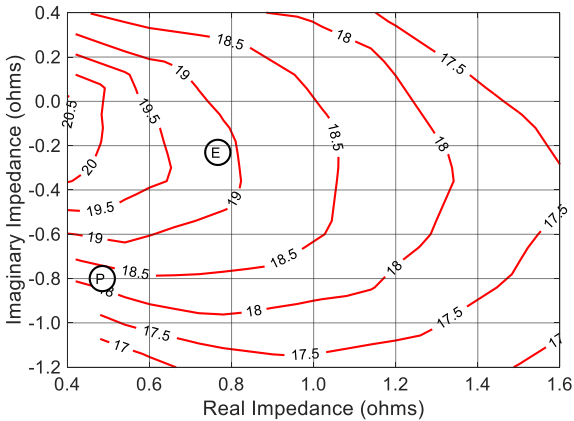
P2.5dB Loadpull Output Power Contours (dBm)



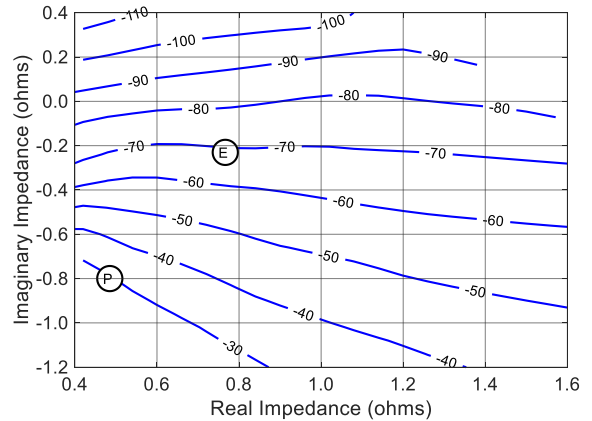
P2.5dB Loadpull Drain Efficiency Contours (%)



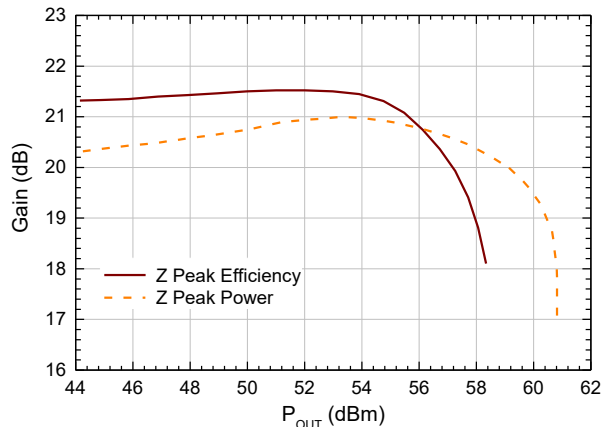
P2.5dB Loadpull Gain Contours (dB)



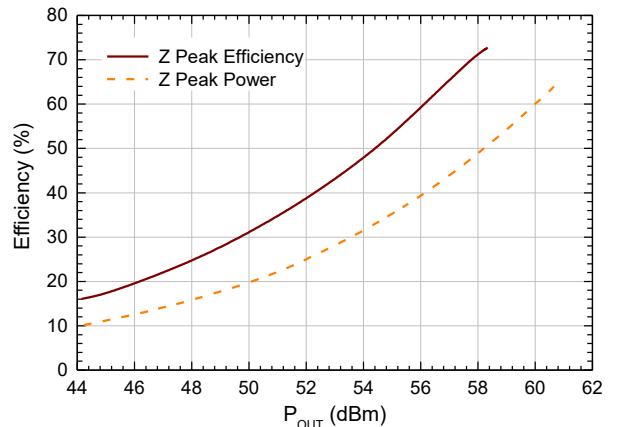
P2.5dB Loadpull AM/PM Contours (°)



Gain vs. Output Power



Drain Efficiency vs. Output Power

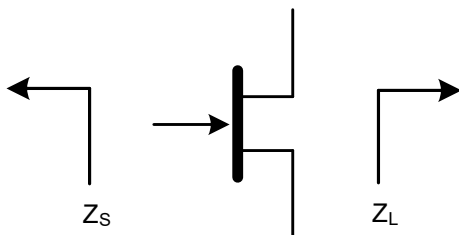


28 V Pulsed¹⁴ Load-Pull Performance - Per Side
Reference Plane at Device Leads

Frequency (MHz)	Z_{SOURCE} (Ω)	Maximum Output Power					
		$V_{DS} = 28\text{ V}, I_{DQ} = 650\text{ mA}, T_C = 25^\circ\text{C}, P_{2.5dB}$					
		Z_{LOAD}^{11} (Ω)	Gain (dB)	P_{OUT} (dBm)	P_{OUT} (W)	η_D (%)	AM/PM ($^\circ$)
960	0.50 - j1.5	0.33 - j0.55	16.1	57.4	554	57.8	-0.2
1030	1.1 - j1.8	0.28 - j0.61	16.4	57.8	607	58.6	-2.6
1090	1.6 + j1.9	0.27 - j0.65	16.0	57.5	567	57.3	-5.0
1215	2.0 - j0.5	0.28 - j0.75	15.6	57.4	550	60.6	-7.8

Frequency (MHz)	Z_{SOURCE} (Ω)	Maximum Drain Efficiency					
		$V_{DS} = 28\text{ V}, I_{DQ} = 650\text{ mA}, T_C = 25^\circ\text{C}, P_{2.5dB}$					
		Z_{LOAD}^{12} (Ω)	Gain (dB)	P_{OUT} (dBm)	P_{OUT} (W)	η_D (%)	AM/PM ($^\circ$)
960	0.50 - j1.5	0.62 - j0.20	17.2	54.8	301	68.3	-7.3
1030	1.1 - j1.8	0.60 - j0.17	16.9	54.5	280	70.8	-12.8
1090	1.6 + j1.9	0.54 - j0.29	16.7	54.3	268	69.3	-21.3
1215	2.0 - j0.5	0.50 - j0.36	16.0	54.5	282	71.6	-10.7

Impedance Reference

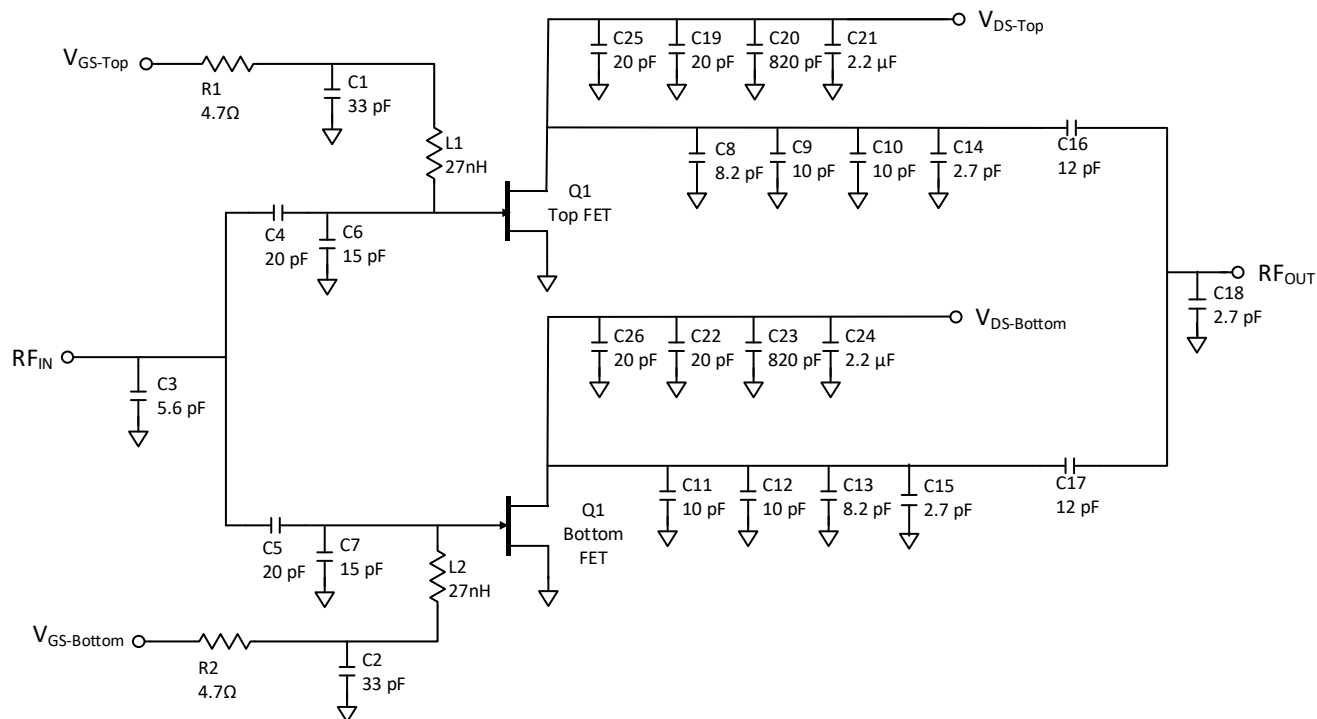


Z_{SOURCE} = Measured impedance presented to the input of the device at package reference plane.

Z_{LOAD} = Measured impedance presented to the output of the device at package reference plane.

- 11. Load Impedance for optimum output power.
- 12. Load Impedance for optimum efficiency.
- 14. Pulse Details: 50 μ s pulse width, 1% duty cycle.

Evaluation Test Fixture and Recommended Tuning Solution 1.03 - 1.09 GHz



Description

Parts measured on evaluation board (20-mil thick RO4350). Matching is provided using a combination of lumped elements and transmission lines as shown in the simplified schematic above. Recommended tuning solution component placement, transmission lines, and details are shown on the next page.

Bias Sequencing*

Turning the device ON

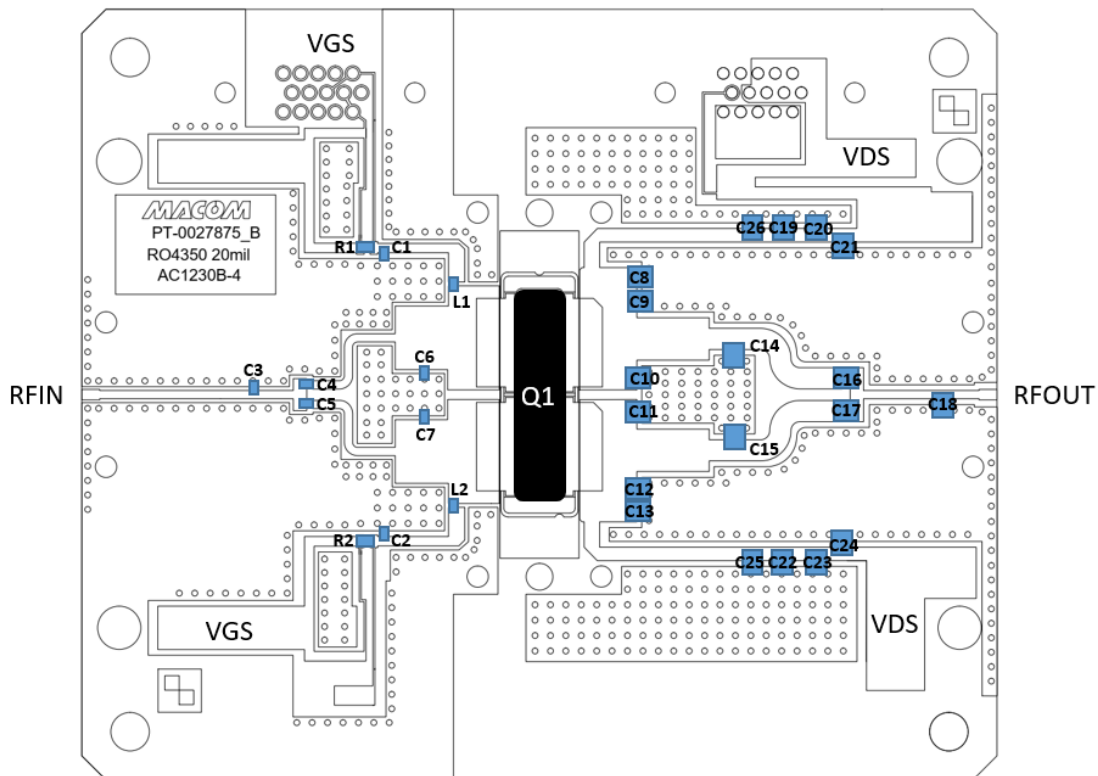
1. Set V_{GS} to pinch-off (V_P).
2. Turn on V_{DS} to nominal voltage (65 V).
3. Increase V_{GS} until I_{DS} current is reached.
4. Apply RF power to desired level.

Turning the device OFF

1. Turn the RF power OFF.
2. Decrease V_{GS} down to V_P pinch-off.
3. Decrease V_{DS} down to 0 V.
4. Turn off V_{GS} .

* For an integrated power management solution please contact MACOM support regarding the MABC-11040.

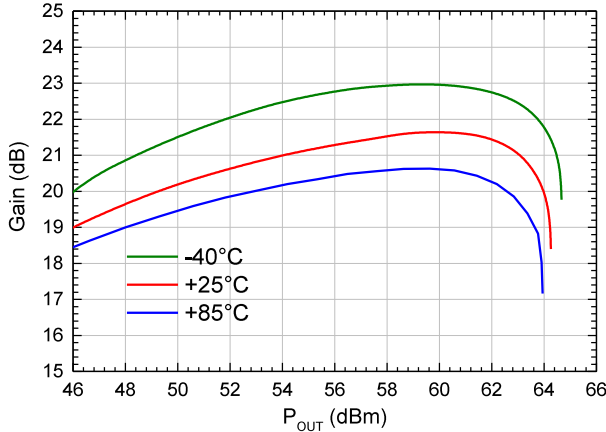
Evaluation Test Fixture and Recommended Tuning Solution 1.03 - 1.09 GHz



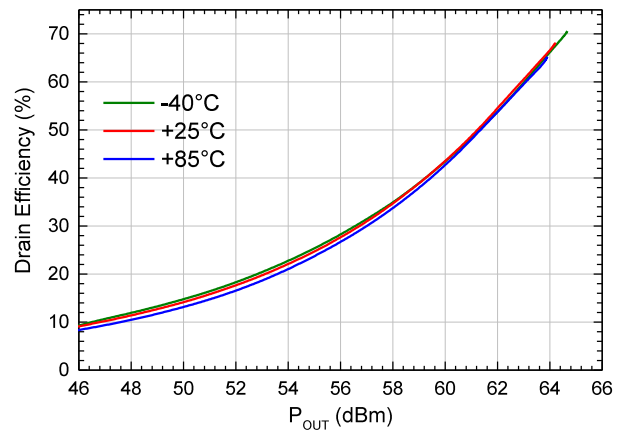
Reference Designator	Value	Tolerance	Manufacturer	Part Number
C1, C2	33 pF	± 5 %	Murata	GQM2195C2E330JB12
C3	5.6 pF	± 0.1 pF	Murata	GQM2195C2E5R6BB12
C4, C5	20 pF	± 5 %	Murata	GQM2195C2E200JB12
C6, C7	15 pF	± 5 %	Murata	GQM2195C2E150JB12
C8, C13	8.2 pF	± 5 %	Murata	GQM22M5C2H8R2JB01
C9 - C12	10 pF	± 5 %	Murata	GQM22M5C2H100JB01
C14, C15, C18	2.7 pF	± 0.1 pF	Murata	GQM22M5C2H2R7BB01
C16, C17	12 pF	± 5 %	Murata	GQM22M5C2H120JB01
C19, C22, C25, C26	20 pF	± 5 %	Murata	GQM22M5C2H200JB01
C20, C23	820 pF	± 5 %	ATC	800B821JT500XT
C21, C24	2.2 μF	± 10 %	Murata	KRM55TR72E225MH01L
L1, L2	27 nH	± 5 %	CoilCraft	1008CS-270XJL
R1, R2	4.7 Ω	± 1 %	Yageo	RT0805FRE074R7L
Q1	MACOM GaN Power Amplifier		MAPC-A1500	
PCB	RO4350, 20 mil, 1 oz. Cu, Au Finish			

Typical Performance Curves as Measured in the 1.03 - 1.09 GHz Evaluation Test Fixture:
Pulsed⁴ 1.06 GHz, $V_{DS} = 65$ V, $I_{DQ} = 1300$ mA, $T_c = 25^\circ\text{C}$ (Unless Otherwise Noted)

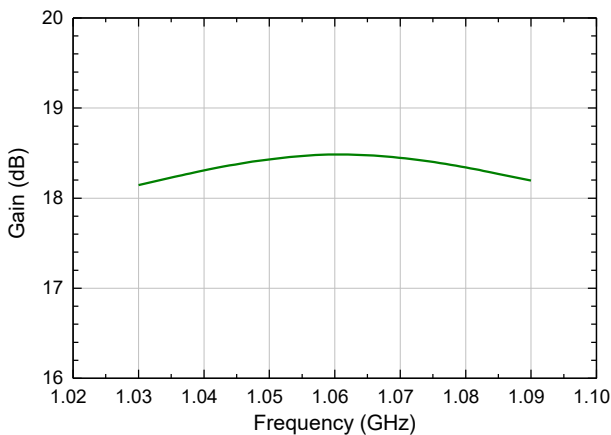
Gain vs. Output Power



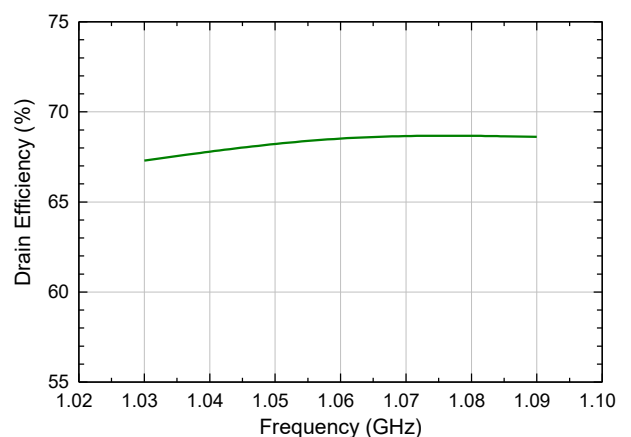
Drain Efficiency vs. Output Power



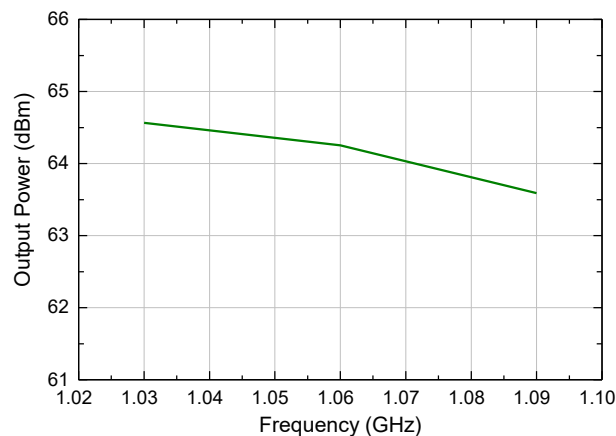
Gain vs. Frequency, 3dB Gain Compression



Drain Efficiency vs. Frequency, 3dB Gain Compression

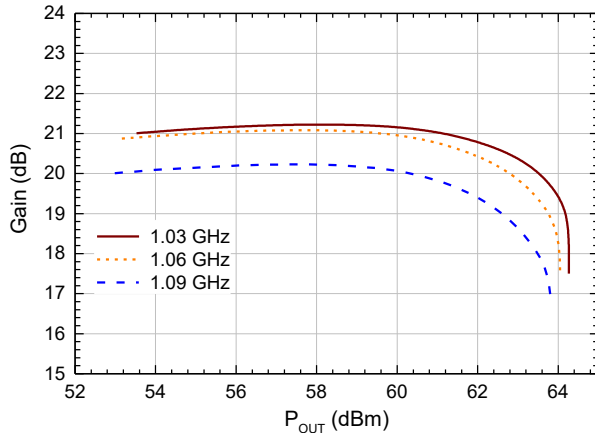


Output Power vs. Frequency, 3dB Gain Compression

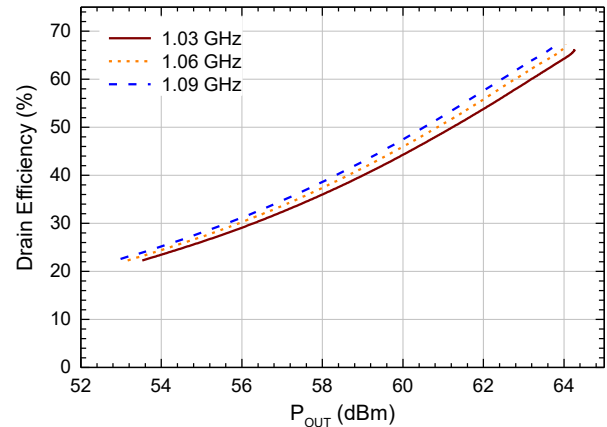


Typical Performance Curves as Measured in the 1.03 - 1.09 GHz Evaluation Test Fixture:
Pulsed⁴ 1.06 GHz, $V_{DS} = 65\text{ V}$, $I_{DQ} = 1300\text{ mA}$, $T_C = 25^\circ\text{C}$ (Unless Otherwise Noted)

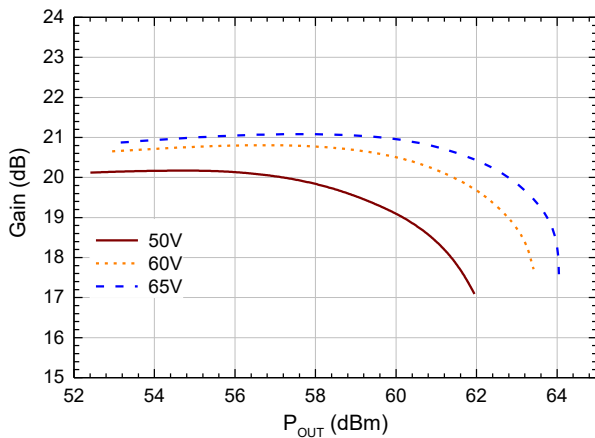
Gain vs. Output Power and Frequency



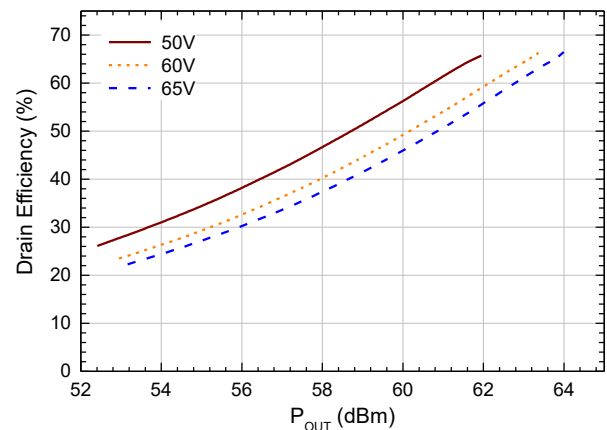
Drain Efficiency vs. Output Power and Frequency



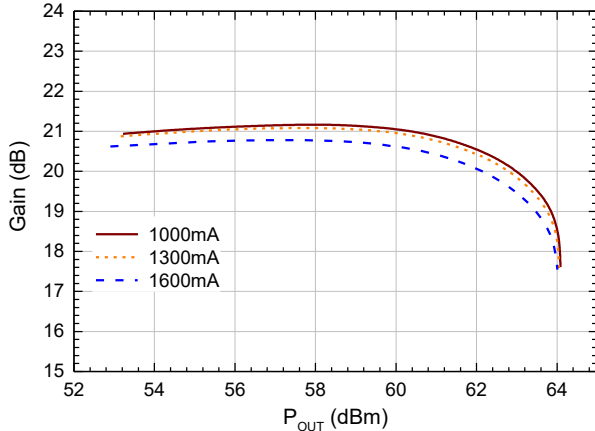
Gain vs. Output Power and V_{DS}



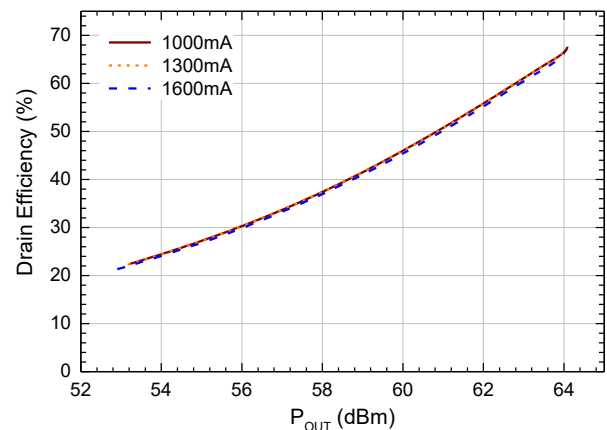
Drain Efficiency vs. Output Power and V_{DS}



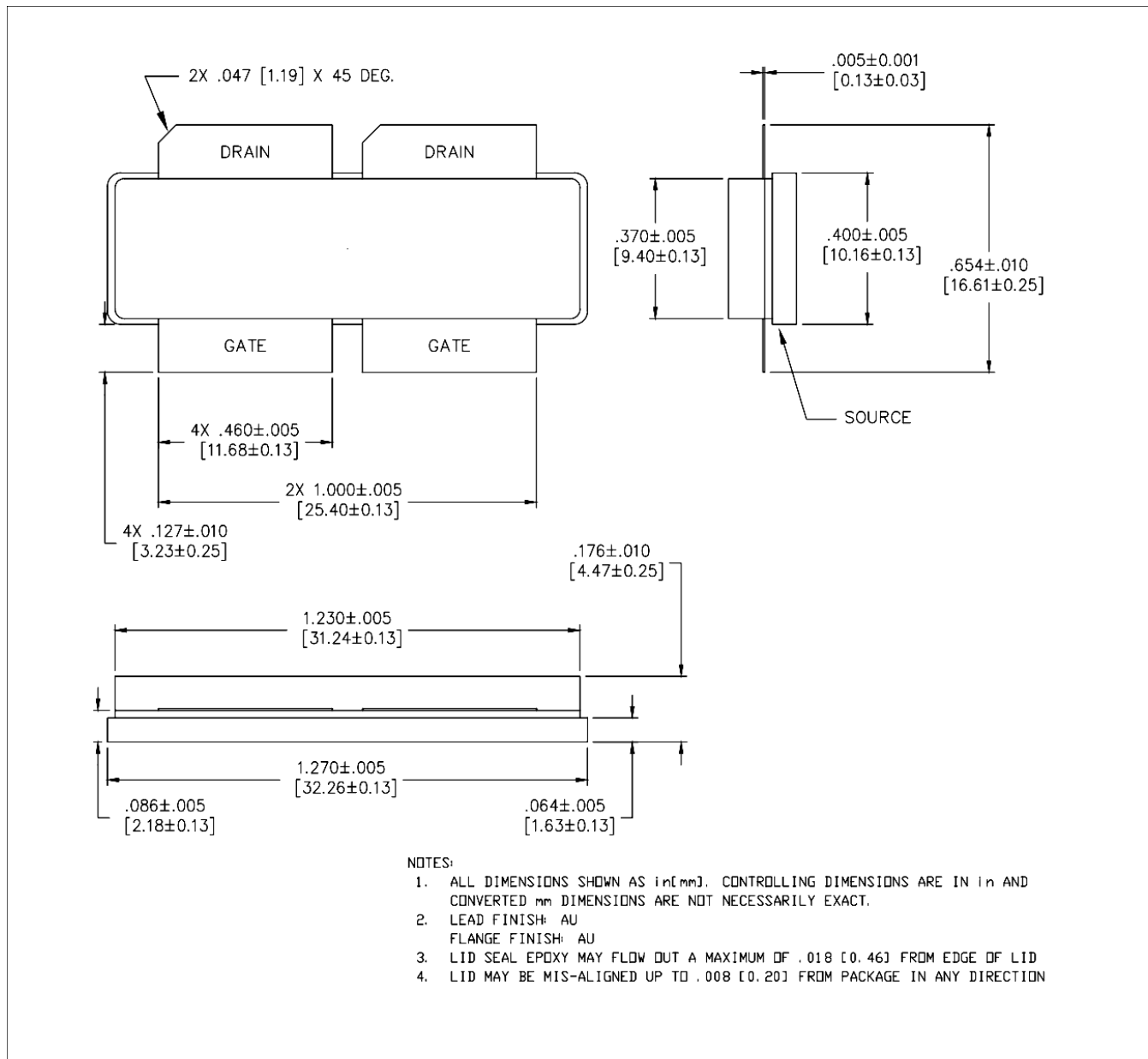
Gain vs. Output Power and I_{DQ}



Drain Efficiency vs. Output Power and I_{DQ}

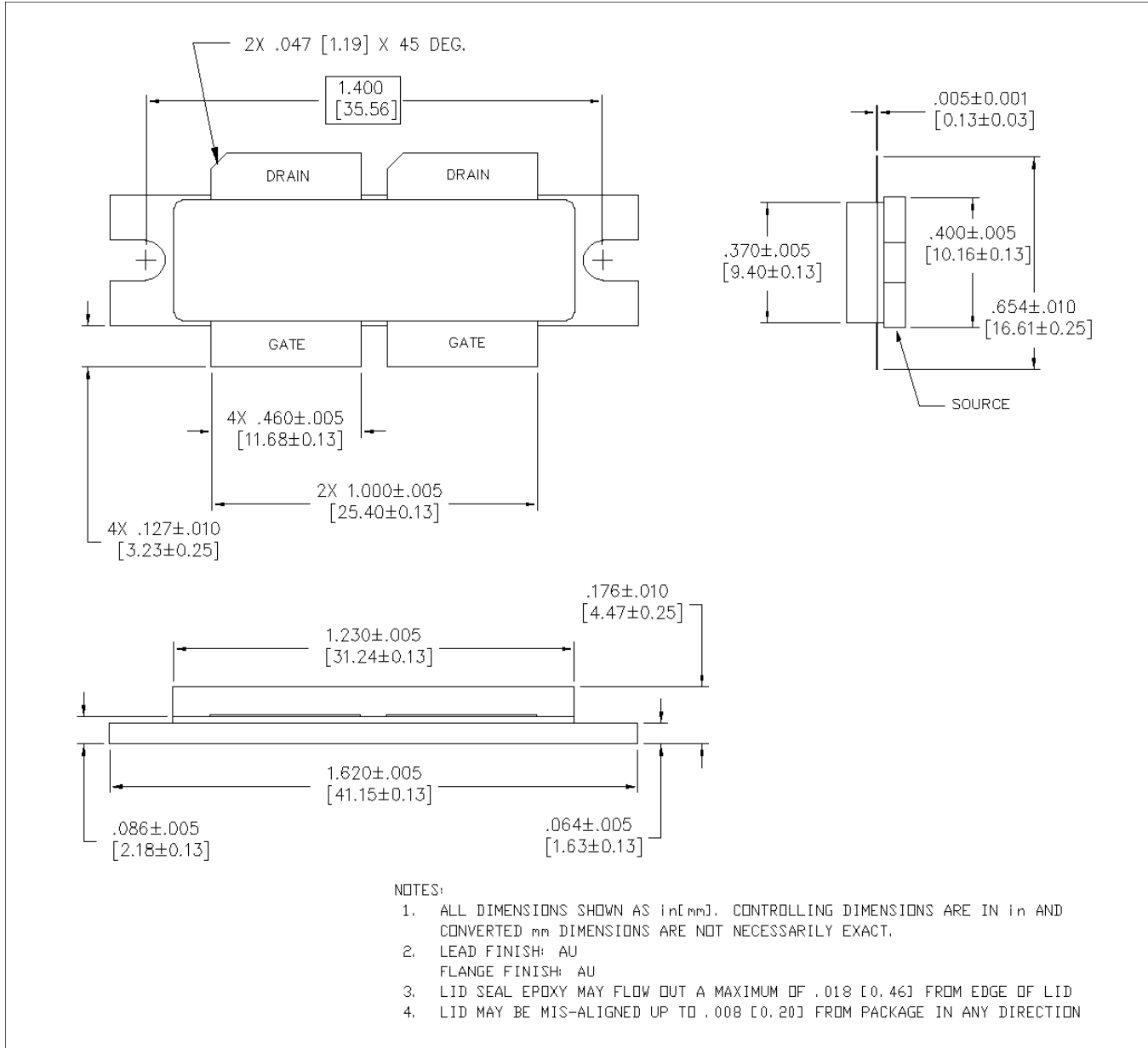


Lead-Free AC-1230S-4 Package Dimensions[†]



[†] Reference Application Note AN0004363 for lead-free solder reflow recommendations.
Meets JEDEC moisture sensitivity level 3 requirements.
Plating is Au.

Lead-Free AC-1230B-4 Package Dimensions[†]



[†] Reference Application Note AN0004363 for lead-free solder reflow recommendations.
Meets JEDEC moisture sensitivity level 3 requirements.
Plating is Au.